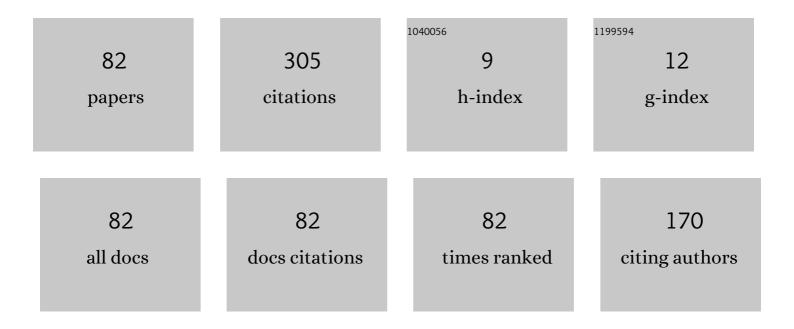
Viktor V Naumov

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Variation of Surface Nanostructures on (100) PbS Single Crystals during Argon Plasma Treatment. Crystals, 2022, 12, 111.	2.2	2
2	Influence of Deposition Conditions and Ion-Plasma Treatment of Thin Cobalt Films on Their Electrical Resistivity. Russian Microelectronics, 2021, 50, 1-7.	0.5	2
3	Determination of Diffusion Coefficients of Lithium in Solid Electrolyte LiPON. Batteries, 2021, 7, 21.	4.5	6
4	Excessive number of high asperities for sputtered rough films. Physical Review B, 2021, 104, .	3.2	5
5	Thin-film solid-state lithium-ion batteries. Materials and technology. Journal of Physics: Conference Series, 2021, 1967, 012043.	0.4	0
6	Thin-Film Solid State Lithium-Ion Batteries of the LiCoC2/LiPON/Si@O@Al System. Russian Microelectronics, 2021, 50, 333-338.	0.5	1
7	Effect of the Etching Profile of a Si Substrate on the Capacitive Characteristics of Three-Dimensional Solid-State Lithium-Ion Batteries. Batteries, 2021, 7, 65.	4.5	0
8	Ion-plasma sputtering of Co and Mo nanometer thin films near the sputtering threshold. Journal Physics D: Applied Physics, 2021, 54, 065204.	2.8	2
9	Study of the Relaxational Polarization Dynamics of the LiPON Solid Electrolyte. Russian Microelectronics, 2020, 49, 345-357.	0.5	4
10	The Influence of Film Thickness on the Annealing-Induced Changes of Texture and of the Fraction of Crystalline Phase in Pt Films. Technical Physics, 2020, 65, 762-770.	0.7	0
11	Testing of aluminium and its alloys as structural materials for a MEMS switch. Microsystem Technologies, 2020, 26, 1971-1980.	2.0	2
12	A Solid-State Lithium-Ion Battery: Structure, Technology, and Characteristics. Technical Physics Letters, 2020, 46, 215-219.	0.7	3
13	Choosing the electrode material for the fast electrochemical actuator. Journal of Physics: Conference Series, 2020, 1695, 012155.	0.4	1
14	Characteristics of an all-solid-state lithium-ion battery prototype. Journal of Physics: Conference Series, 2020, 1695, 012193.	0.4	0
15	The Influence of Low-Energy Ion-Plasma Treatment on the Surface Morphology of Pt Films with Varying Strength of Crystalline Texture. Journal of Surface Investigation, 2020, 14, 777-783.	0.5	3
16	Surface Modification of Pb1 – xSnxSe Films during Plasma Treatment Near the Sputtering Threshold. Journal of Surface Investigation, 2020, 14, 1174-1178.	0.5	2
17	The Influence of Diffusion Barriers on the Capacitance Properties of Composite Anodes with Si–CuSi–Cu Composition. Technical Physics Letters, 2020, 46, 943-946.	0.7	0
18	A fast electrochemical actuator in the non-explosive regime. Journal of Micromechanics and Microengineering, 2019, 29, 114001.	2.6	5

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19	Plasma-assisted surface nanostructuring of epitaxial Pb _{1â^'<i>x</i>} Sn _{<i>x</i>} Te (0 ≤i>x ≤) films. Semiconductor Science and Technology, 2019, 34, 095001.	2.0	6
20	Structural Changes in Si–CuSi Films upon Intercalation of Lithium Ions. Technical Physics Letters, 2019, 45, 973-976.	0.7	1
21	Impact of plasma nanostructuring on the electrical properties of Cu(In,Ca)Se2 films. Journal of Physics: Conference Series, 2019, 1238, 012040.	0.4	0
22	Formation of Nanoporous Copper-Silicide Films. Semiconductors, 2019, 53, 395-399.	0.5	6
23	Effect of the Pressure of Oxygen on the Plasma Oxidation of the Titanium Nitride Surface. Russian Microelectronics, 2019, 48, 402-408.	0.5	2
24	Degradation of Titanium Electrodes in the Alternating Polarity Electrolysis. International Journal of Electrochemical Science, 2019, , 5211-5225.	1.3	8
25	Optimization of electrodes for the fast electrochemical actuator. Journal of Physics: Conference Series, 2019, 1410, 012197.	0.4	1
26	Contact resistance and lifecycle of a single- and multiple-contact MEMS switch. Microsystem Technologies, 2019, 25, 4135-4141.	2.0	8
27	The Influence of Film Thickness on Annealing-Induced Grain Growth in Pt Films. Technical Physics, 2018, 63, 900-907.	0.7	5
28	The Formation of Hollow Lead Structures on the Surface of PbSe Films Treated in Argon Plasma. Technical Physics Letters, 2018, 44, 518-521.	0.7	11
29	Surface nanostructuring of Culn _{1â^'<i>x</i>} Ga _{<i>x</i>} Se ₂ films using argon plasma treatment. Semiconductor Science and Technology, 2017, 32, 075014.	2.0	6
30	New plasma-assisted approach to the fabrication of Cu(In,Ga)(S,Se)2nanowires. Journal of Physics: Conference Series, 2017, 816, 012028.	0.4	0
31	Influence of a static magnetic field on the formation of silicide phases in a Cu/Si(100) structure upon isothermal annealing. Semiconductors, 2017, 51, 812-816.	0.5	3
32	An experimental examination of thin films of lithium phosphorus oxynitride (a solid electrolyte). Technical Physics Letters, 2017, 43, 503-506.	0.7	2
33	Fast electrochemical membrane actuator: Design, fabrication and preliminary testing. Journal of Physics: Conference Series, 2017, 917, 082006.	0.4	1
34	Development of the Technology of Magnetron Sputtering Deposition of LiPON Films and Investigation of Their Characteristics. Russian Microelectronics, 2017, 46, 424-432.	0.5	2
35	The study of effect of solid electrolyte on charge-discharge characteristics of thin-film lithium-ion batteries. Journal of Physics: Conference Series, 2017, 917, 032030.	0.4	0
36	Resistive contact MEMS switch in a "hot―operation mode. Journal of Physics: Conference Series, 2017, 917, 082001.	0.4	3

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37	Plasmaâ€assisted selfâ€formation of nanotip arrays on the surface of Cu(In,Ga)Se ₂ thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1600135.	0.8	4
38	A simple electrochemical micropump: Design and fabrication. Journal of Physics: Conference Series, 2016, 741, 012167.	0.4	13
39	A low actuation voltage bistable MEMS switch: design, fabrication and preliminary testing. Proceedings of SPIE, 2016, , .	0.8	1
40	Plasma sputtering of Pb1–x Eu x Te films with varied composition and structure. Journal of Surface Investigation, 2016, 10, 623-626.	0.5	3
41	Changes in the conductivity of lead-selenide thin films after plasma etching. Semiconductors, 2016, 50, 1125-1129.	0.5	4
42	Low energy selective etching of metal films in oxygen-containing high-density argon plasma. Journal of Surface Investigation, 2016, 10, 855-859.	0.5	9
43	Secondary ion mass spectrometry study of the formation of a nanometer oxide film on a titanium nitride surface. Russian Microelectronics, 2016, 45, 242-255.	0.5	5
44	MEMS switch with the active contact breaking mechanism. Journal of Physics: Conference Series, 2015, 643, 012091.	0.4	0
45	Problems of the experimental implementation of MTJ. Journal of Physics: Conference Series, 2015, 643, 012105.	0.4	2
46	Cyclic voltammetry studies of silicon–aluminum thin-film electrodes synthesized in the presence of oxygen. Russian Journal of Electrochemistry, 2015, 51, 1157-1161.	0.9	7
47	Application of abnormally high sputtering rate of PbTe(Te) single crystals during inductively coupled argon plasma treatment for fabrication of nanostructures. Semiconductor Science and Technology, 2015, 30, 035017.	2.0	7
48	Plasma sputtering of polycrystalline Pb1â^'xSnxTe thin films grown on glass substrates using hot wall deposition. Semiconductor Science and Technology, 2014, 29, 075020.	2.0	3
49	Electrostatically actuated MEMS switch with resistive contact. Proceedings of SPIE, 2014, , .	0.8	1
50	Effect of technological factors on the micromagnetic states of magnetic nanostructures. Bulletin of the Russian Academy of Sciences: Physics, 2014, 78, 13-15.	0.6	1
51	Investigations of nanocrystalline SnS films' surface morphology modification during inductively coupled argon plasma sputtering. Semiconductor Science and Technology, 2014, 29, 015009.	2.0	18
52	Features of the plasma sputtering of polycrystalline Pb1 â^' x Sn x S films. Journal of Surface Investigation, 2014, 8, 602-606.	0.5	3
53	Formation of W/HfO2/Si gate structures using in situ magnetron sputtering and rapid thermal annealing. Technical Physics, 2014, 59, 711-715.	0.7	1
54	Magnetomigration effect during the annealing of granular cobalt-copper films. Technical Physics Letters, 2014, 40, 145-148.	0.7	1

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55	Self-formation of lead telluride nanostructures during argon plasma etching of single-crystal wafers. Journal of Physics: Conference Series, 2014, 541, 012017.	0.4	1
56	Resonance properties of metallic nanocantilevers. Journal of Physics: Conference Series, 2014, 541, 012018.	0.4	0
57	Magnetomigration in granular cobalt-copper films deposited by the ion-plasma method. Technical Physics Letters, 2013, 39, 556-559.	0.7	2
58	The effect of ion energy on the surface morphology of platinum film under high-frequency ion plasma sputtering. Technical Physics Letters, 2013, 39, 130-133.	0.7	3
59	Dynamics of oxide phases on the surface of single- and polycrystalline Pb1 â ^{~,} x Sn x Te films upon their investigation by the raman light scattering method. Optics and Spectroscopy (English Translation of) Tj ETQq1 1	0.7&4314	r g BT /Overic
60	Resonance properties of multilayer metallic nanocantilevers. , 2013, , .		2
61	Features of formation of high- <i>k</i> dielectric layer in w/ultrathin HfO ₂ /Si (100) structures under annealing. Proceedings of SPIE, 2013, , .	0.8	1
62	Investigations of the inductively coupled argon plasma sputtering of Pb1 â^' x Sn x Te ternary solid solution. Journal of Surface Investigation, 2012, 6, 643-646.	0.5	6
63	Investigations of the pore formation in the lead selenide films using glacial acetic acid- and nitric acid-based electrolyte. Nanoscale Research Letters, 2012, 7, 338.	5.7	4
64	Formation and investigation of cobalt silicide ultrathin layers in Ti/Co/Ti-, TiN/Ti/Co-, and TiN/Co-on-silicon structures. Technical Physics, 2012, 57, 279-285.	0.7	2
65	Features of CoSi2 phase formation by two-stage rapid thermal annealing of Ti/Co/Ti/Si(100) structures. Technical Physics Letters, 2011, 37, 112-115.	0.7	8
66	Lead selenide nanowire growth by vapor-liquid-solid mechanism under mask during plasma processing. Technical Physics Letters, 2011, 37, 929-931.	0.7	11
67	Formation of thin-film HfO2/Si(100) structures by high-frequency magnetron sputtering. Russian Microelectronics, 2011, 40, 383-388.	0.5	3
68	Control of the formation of ultrathin CoSi2 layers during the rapid thermal annealing of Ti/Co/Ti/Si(100) structures. Russian Microelectronics, 2011, 40, 389-394.	0.5	5
69	Fabrication and study of porous PbTe layers on silicon substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1801-1804.	0.8	7
70	Investigations of PbSe layers after anodic electrochemical etching by scanning electron microscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1918-1922.	0.8	4
71	Fabrication of porous nanostructured lead chalcogenide semiconductors for modern thermoelectric and optoelectronic applications. Journal of Physics: Conference Series, 2011, 291, 012023.	0.4	5
72	CoSi 2 /TiO 2 /SiO 2 /Si gate structure formation. , 2009, , .		0

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73	Enhancement of the transversal magnetooptical Kerr effect in nanoperforated cobalt films. Technical Physics Letters, 2009, 35, 589-593.	0.7	9
74	Dependence of the transversal magneto-optic Kerr effect on the incidence angle of light for ultrathin films of cobalt and Co/Cu/Co multilayers. Russian Microelectronics, 2009, 38, 251-256.	0.5	1
75	An automated stand for express-diagnostics of magnetoresistive structures. Russian Microelectronics, 2009, 38, 257-259.	0.5	1
76	Magnetoresistance of multilayered structures obtained by the magnetron method. Russian Microelectronics, 2009, 38, 334-338.	0.5	0
77	Increasing adhesion of metallic films to silicon by ion bombardment during growth. Technical Physics, 2009, 54, 1072-1075.	0.7	1
78	<title>Simulation, fabrication, and dynamics characteristics of electrostatically actuated
switches</title> . , 2008, , .		1
79	Structural properties of Pb1â^'xEuxSe/CaF2/Si (1 1 1). Semiconductor Science and Technology, 2007, 22 1317-1322.	2.0	12
80	Effect of low-energy ion bombardment on the crystal structure and superconductivity of niobium films. Technical Physics, 2004, 49, 426-430.	0.7	1
81	The effect of low-energy ion bombardment on the density and crystal structure of thin films. Technical Physics, 2001, 46, 1020-1025.	0.7	11
82	Growth and properties of PbTe films on porous silicon. Infrared Physics and Technology, 1999, 40, 337-342.	2.9	15